HFZT

2SD2114

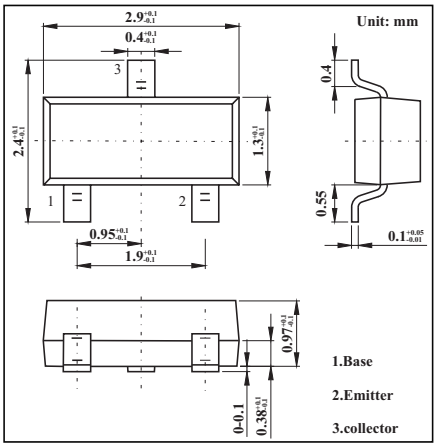
SOT-23 Plastic-Encapsulate Transistors

FEATURES

- High DC current gain
- High emitter-base voltage
- Low VCE (sat)

MECHANICAL DATA

- Case style:SOT-23molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-base voltage	V_{CBO}	25	V
Collector-emitter voltage	V_{CEO}	20	V
Emitter-base voltage	V_{EBO}	12	V
Collector current	I_C	0.5	A
		1	
Collector power dissipation	P_C	0.2	W
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 ~ +150	℃

* Single pulse Pw=100ms

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	B_{VCBO}	I_C=10uA	25			V
Collector-emitter breakdown voltage	B_{VCEO}	I_C=1mA	20			V
Emitter-base breakdown voltage	B_{VEBO}	I_E=10uA	12			V
Collector cutoff current	I_{CBO}	V_{CB}=20V			0.5	A
Emitter cutoff current	I_{EBO}	V_{EB}=10V			0.5	A
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C/I_B=500mA/20mA		0.18	0.4	V
DC current transfer ratio	h_{FE}	V_{CE}=3V,I_C=10mA	820		2700	
Output capacitance	f_T	V_{CE}=10V,I_E=-50mA,f=100MHz		350		MHz
Transition frequency	C_{ob}	V_{CB}=10V,I_E=0,f=1MHz		8.0		pF
Output On-resistance	R_{on}	I_B=1mA,V_i=100mV(rms),f=1kHz		0.8		

*Measured using pulse current